

SAMTM Data Sheet SAM-1064-50-12ps-x, λ = 1064 nm

Laser wavelength $\lambda = 1064 \text{ nm}$

High reflection band $\lambda = 1010 ... 1110 \text{ nm}$

Absorbance $A_0 = 50 \%$ Modulation depth $\Delta R = 40 \%$ Non-saturable loss $A_{ns} = 10 \%$

Saturation fluence $\Phi_{\text{sat}} = 19 \,\mu\text{J/cm}^2$

Relaxation time constant $\tau \sim 12 \text{ ps}$

Damage threshold $\Phi = 800 \,\mu\text{J/cm}^2$

Chip area 4.0 mm x 4.0 mm; other dimensions on request

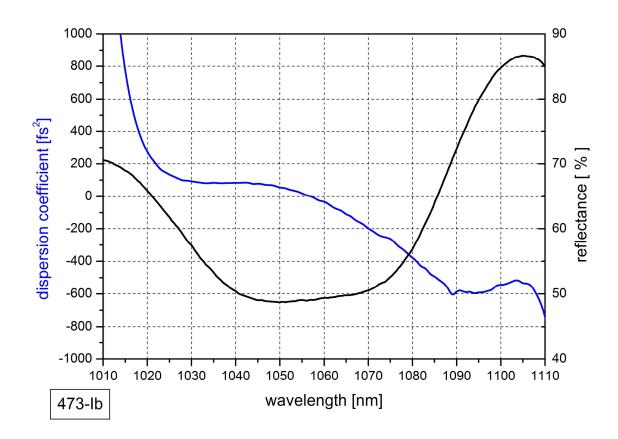
Chip thickness 450 µm

Protection the SAM is protected with a dielectric front layer

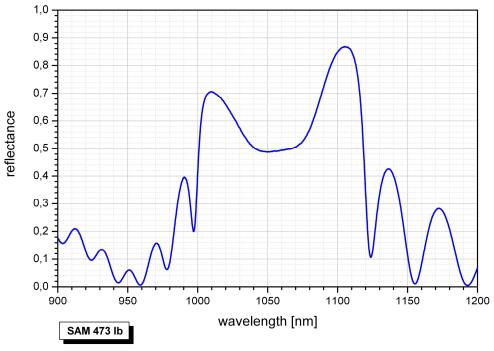
Mounting option **x** denotes the type of mounting as follows:

x = 0
x = 12.7 g
x = 25.4 g
x = 12.7 s
x = 25.4 s
x

Low intensity spectral reflectance and dispersion coefficient D₂



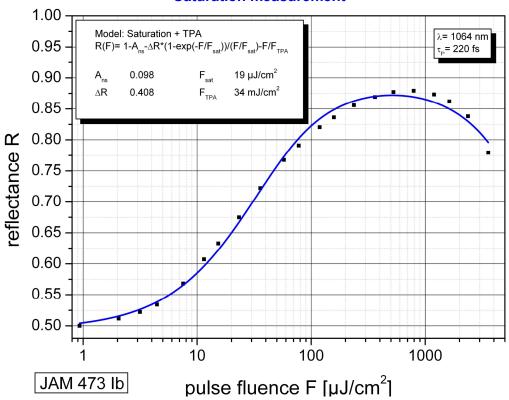




Group Delay Dispersion (GDD)

Dispersion coefficient
$$D_2(\omega)=\frac{\partial^2\varphi}{\partial\omega^2}$$
 with φ - reflected phase
$$\omega=2\pi\frac{c}{\lambda}$$
 - angular frequency

Saturation measurement





Pump-probe measurement

